TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

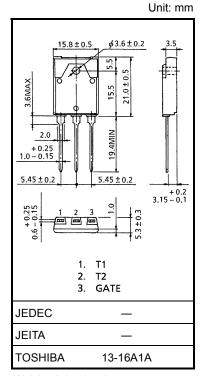
SM16GZ51, SM16JZ51

AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage: VDRM = 400V, 600 V
- R.M.S On-State Current: IT (RMS) = 16 A
- High Commutating (dv / dt): (dv / dt) $c = 10 \text{ V} / \mu \text{s}$
- Isolation Voltage: VISOL = 1500 V AC

MAXIMUM RATINGS

CHARACTER	ISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	SM16GZ51	\/	400	V	
	SM16JZ51	V_{DRM}	600		
R. M. S. On-state Curro (Full Sine Waveform Ta		I _{T (RMS)}	16	А	
Peak One Cylce Surge On-State Current (Non-Repetitive)		l-o.	150 (50 Hz)	А	
		ITSM	165 (60 Hz)		
I ² t Limit Value		I ² t	112.5	A ² s	
Critical Rate of Rise of Current	On-State (Note 1)	di / dt	50	Α/μs	
Peak Gate Power Dissi	pation	P_{GM}	5	W	
Average Gate Power D	issipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V_{GM}	10	V	
Peak Gate Current		I _{GM}	2	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature R	lange	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1 min.)	V _{ISOL}	1500	V	



Weight: 2.0 g (typ.)

Note 1: di / dt test condition

 V_{DRM} = 0.5 × Rated, $I_{TM} \le 25$ A, $t_{gw} \ge 10$ μ s, $t_{gr} \le 250$ ns, i_{gp} = I_{GT} × 2.0

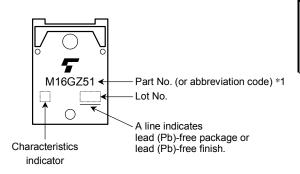


ELECTRICAL CHARACTERISTICS (Ta = 25°C)

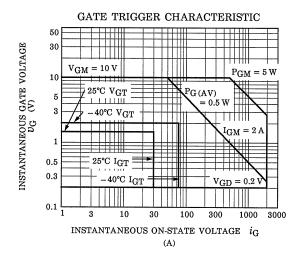
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μA
Gate Trigger Voltage	1	V _{GT}	V _D = 12 V, R _L = 20 Ω	T2 (+) , Gate (+)	_	_	1.5	V
	П			T2 (+), Gate (-)	_	_	1.5	
	III			T2 (-) , Gate (-)	_	_	1.5	
	IV			T2 (-) , Gate (+)	_	_	_	
Gate Trigger Current	- 1	- I _{GT}	V _D = 12 V, R _L = 20 Ω	T2 (+), Gate (+)	_	_	30	- mA
	Ш			T2 (+), Gate (-)	_	_	30	
	III			T2 (-) , Gate (-)	_	_	30	
	IV			T2 (-), Gate (+)	_	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 25 A		_	_	1.5	V
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V
Holding Current		lΗ	V _D = 12 V, I _{TM} = 1 A		_	_	50	mA
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC		_	_	1.8	°C/W
Critical Rate of Rise of Off-State Voltage		dv / dt	V _{DRM} = Rated, T _j = 125°C Exponential Rise		_	300	_	V / µs
Critical Rate of Rise of Off-State Voltage at Commutation ((dv / dt) c	V _{DRM} = 400 V, T _j = 125°C (di / dt) c = -8.7 Å / ms		10	_	_	V / µs

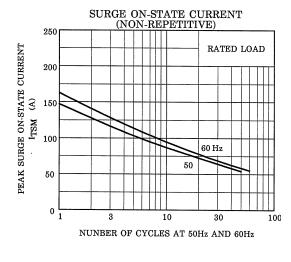
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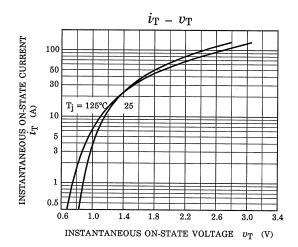
MARKING

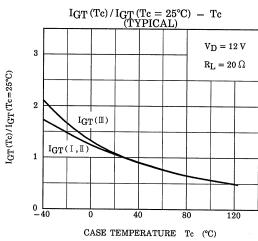


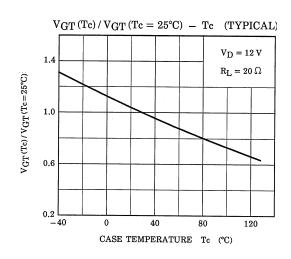
	Part No. (or abbreviation code)	Part No.		
*1	M16GZ51	SM16GZ51		
	M16JZ51	SM16JZ51		

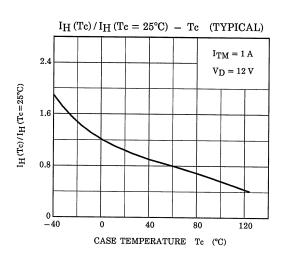


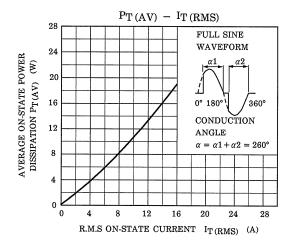


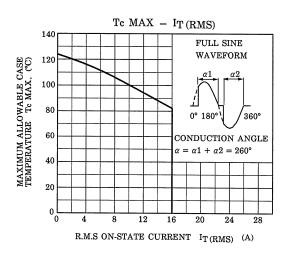


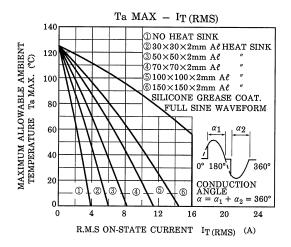


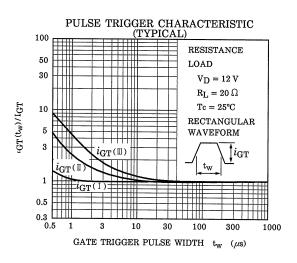


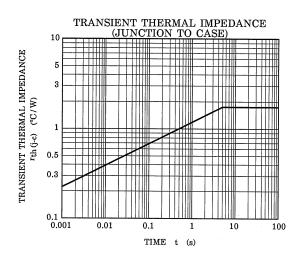












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